Figure Captions

Fig.1. Pressure and temperature variation of relative resistivity for Russian (1) and German (2) manganin

Fig.2. Pressure variation of the relative changes of the pressure sensitivity coefficient for Russian manganin sensors (1,2,3)

Fig.3. Pressure variation of resistivity for two tellurium monocrystals
1,2 - $a^{*} = 1{\cdot}75 \times 10^{-5}$ eV/atm (R_o = 19,6 ohm)
3,4 - $a^{*} = 1{\cdot}48 \times 10^{-5}$ eV/atm (R_o = 6,5 ohm)

Fig.4. $I_c = f(V_c)$ as a function of pressure and temperature for a planar transistor (OE connection)
1 - P_{atm}, 20°C; 2 - P_{atm}, 22°C; 3 - 4000 atm, 20°C;
4 - P_{atm}, 24°C; 5 - 4000 atm, 22°C; 6 - P_{atm}, 26°C;
7 - 4000 atm, 24°C; 8 - 4000 atm, 26°C.

Fig.5. The relative changes of V_{BE} as a function of pressure for a planar transistor (OE connection)
1,2,3 - transistor 12; I_B: 30, 20, 10 μA
4,5,6 - transistor 13; I_B: 30, 20, 10 μA
7,8,9 - transistor 12; I_C: 2 mA, 500 μA, 100 μA.

Fig.6. $I_C = f(U_{BE})$ for a planar transistor (OE connection)
1 - atmospheric pressure; 2 - 6000 atm

Fig.7. The relative changes of U_{BE} as a function of temperature for a planar transistor (OE connection)
1,2,3, - I_C = 2 mA; P : atmospheric, 2500 atm, 5000 atm
4,5,6 - I_C = 500 μA; P : atmospheric, 2500 atm, 5000 atm

Fig.8. Coefficient of pressure quality for electric sensors
1,2,3 - manganin sensors (item 1,2 and 3 in Table 2)
4,5,6,7 - Te, InSb sensors (item 4,5,6 and 7 in Table 2)
10, 11 - planar transistor sensor (item 10 and 11 in Table 2).

Table 1.

Values of Coefficients a,b,c in Eq.2
(in the temperature range 0 - 50°C)

	Electric Sensor	a x 10^{-7} [deg^{-2}]	b x 10^{-5} [deg^{-1}]	c x 10^{-4}	$(\frac{\Delta R}{R_o})_{max}$ x 10^{-5}	t_{max} [deg]
1	German manganin at atmospheric pressure†	-4·1	1·26	-0·88	0·88	15·4
2	German manganin at 6000 atm	-3·57	1·82	-2·2	1·07	25·5
3	Russian manganin before heat treatment	-6·2	3·5	-4·5	4·25	28·2
4	Russian manganin after heat treatment	-4·65	2·38	-2·91	1·42	25·6
5	Russian manganin as in (4) at 3000 atm and 6000 atm	-4·1	3·11	-4·58	12·8	37·8
6	German-Russian manganin sensor‡	-4·35	1·82	-1·89	0·06	21·0
7	Te* (selected crystal)	-540	350	-490	770	32·4
8	InSb* (selected crystal)	0	-0·085	1700	-	-
9	Te + InSb**	-500	260	-330	126	26·0

†Before and after heat treatment.

‡Sensor constructed by Czaputowicz by connecting German and Russian manganin (as in items (2) and (4)).

*In the temperature range 15 - 30°C.

**Monocrystals Te ($R_{Te} \approx 12.5$ ohm) and InSb ($R_{InSb} \approx 1$ ohm) connected in series.